

ABSTRACT

A semiconductor device and a fabrication method thereof in which the semiconductor device includes capacitors having a metal/insulator/metal (MIM) structure are disclosed. The method includes forming an interlayer insulating film on a structure of a semiconductor substrate that exposes lower wiring and a lower insulating film; selectively etching the interlayer insulating film to form a first electrode opening that exposes the lower wiring; forming a first electrode in the first electrode opening such that the first electrode opening is filled; selectively etching the interlayer insulating film at a region of the same adjacent to the first electrode to thereby form a second electrode opening; forming a dielectric layer along inner walls that define the second electrode opening; forming a second electrode on the dielectric layer in such a manner to fill the second electrode opening; and forming upper wiring on at least a portion of the second electrode.